

MOS FIELD EFFECT TRANSISTOR 2SK3635

SWITCHING N-CHANNEL POWER MOS FET

DESCRIPTION

The 2SK3635 is N-channel MOS FET device that features a low on-state resistance and excellent switching characteristics, and designed for high voltage applications such as DC/DC converter.

→ ORDERING INFORMATION

PART NUMBER	PACKAGE
2SK3635	TO-251 (MP-3)
2SK3635-Z	TO-252 (MP-3Z)

FEATURES

- High voltage: V_{DSS} = 200 V
- Gate voltage rating: ±30 V
- · Low on-state resistance

 $R_{DS(on)} = 0.43 \Omega MAX. (V_{GS} = 10 V, I_{D} = 4.0 A)$

- Low Ciss: Ciss = 390 pF TYP.
- · Built-in gate protection diode
- TO-251/TO-252 package
- · Avalanche capability rated

(TO-251)



(TO-252)



ABSOLUTE MAXIMUM RATINGS (TA = 25°C)

Drain to Source Voltage (V _{GS} = 0 V)	VDSS	200	V
Gate to Source Voltage (V _{DS} = 0 V)	Vgss	±30	V
Drain Current (DC) (Tc = 25°C)	ID(DC)	±8.0	Α
Drain Current (pulse) Note1	ID(pulse)	±24	Α
Total Power Dissipation (Tc = 25°C)	P _{T1}	24	W
Total Power Dissipation (T _A = 25°C)	P _{T2}	1.0	W
Channel Temperature	Tch	150	°C
Storage Temperature	Tstg	-55 to +150	°C
Single Avalanche Current Note2	las	8	Α
Single Avalanche Energy Note2	Eas	6.4	mJ
Repetitive Avalanche Current Note3	lar	8	Α
Repetitive Avalanche Energy Note3	Ear	2.4	mJ

Notes 1. PW \leq 10 μ s, Duty Cycle \leq 1%

- **2.** Starting Tch = 25°C, VdD = 100 V, Rg = 25 Ω , Vgs = 20 \rightarrow 0 V, L = 100 μ H
- **3.** Tch \leq 125°C, Rg = 25 Ω , VDD = 100 V

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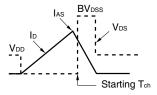


查询ECHRICAL CHARACTERISTICS (TA = 25°C)

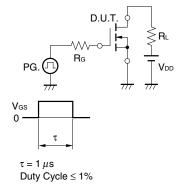
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	IDSS	V _{DS} = 200 V, V _{GS} = 0 V			10	μΑ
Gate Leakage Current	Igss	V _{GS} = ±30 V, V _{DS} = 0 V			±10	μΑ
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1 mA	2.5	3.5	4.5	V
Forward Transfer Admittance	y fs	V _{DS} = 10 V, I _D = 4.0 A	3	5		S
Drain to Source On-state Resistance	RDS(on)	V _{GS} = 10 V, I _D = 4.0 A		0.34	0.43	Ω
Input Capacitance	Ciss	V _{DS} = 10 V		390		pF
Output Capacitance	Coss	V _{GS} = 0 V		95		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		45		pF
Turn-on Delay Time	t d(on)	V _{DD} = 100 V, I _D = 4.0 A		5		ns
Rise Time	t r	V _{GS} = 10 V		7		ns
Turn-off Delay Time	t d(off)	$R_G = 0 \Omega$		19		ns
Fall Time	t f			6		ns
Total Gate Charge	QG	V _{DD} = 160 V		12		nC
Gate to Source Charge	Qgs	V _{GS} = 10 V		2		nC
Gate to Drain Charge	Q _{GD}	I _D = 8.0 A		6		nC
Body Diode Forward Voltage	V _{F(S-D)}	I _F = 8 A, V _{GS} = 0 V		1.0		V
Reverse Recovery Time	trr	I _F = 8 A, V _{GS} = 0 V		110		ns
Reverse Recovery Charge	Qrr	di/dt = 100 A/μs		360		nC

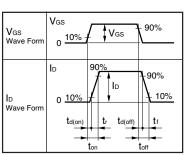
TEST CIRCUIT 1 AVALANCHE CAPABILITY

$\begin{array}{c|c} D.U.T. \\ \hline PG. \\ \hline \end{array} \begin{array}{c} S & S & S \\ \hline \end{array} \begin{array}{c} S \\ \hline \end{array} \begin{array}{c} S & S \\ \hline \end{array} \begin{array}{c} S \\ \end{array} \begin{array}{c} S \\ \hline \end{array} \begin{array}{c} S \\ \hline$



TEST CIRCUIT 2 SWITCHING TIME

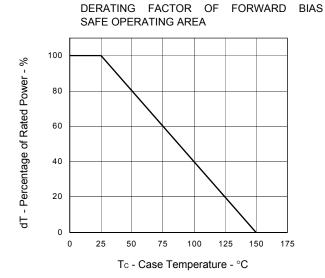


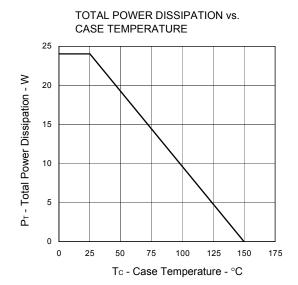


TEST CIRCUIT 3 GATE CHARGE

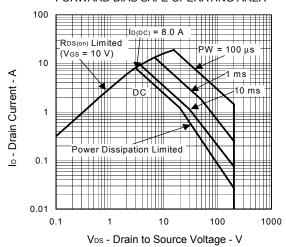


查询Piekiecitatacone RISTICS (TA = 25°C)

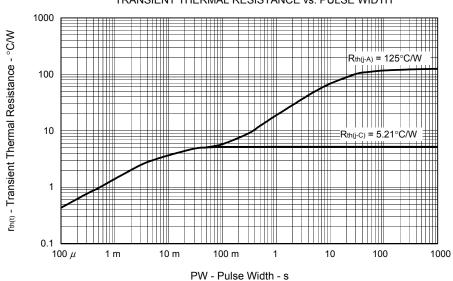




FORWARD BIAS SAFE OPERATING AREA

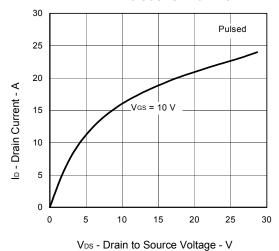


TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

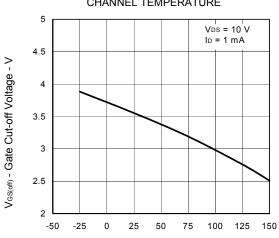


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查询"2SK3635"(快迎商URRENT vs. DRAIN TO SOURCE VOLTAGE

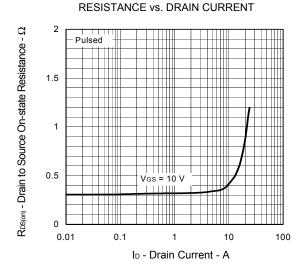


GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE

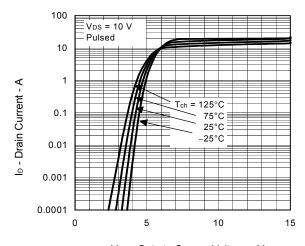


DRAIN TO SOURCE ON-STATE

Tch - Channel Temperature - °C

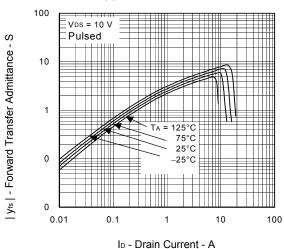


FORWARD TRANSFER CHARACTERISTICS

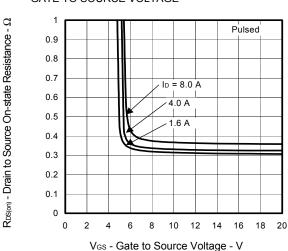


V_{GS} - Gate to Source Voltage - V

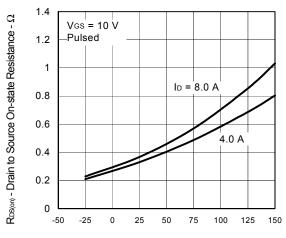
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE

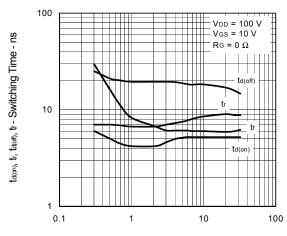


查询"2\$网络05"0共应商E ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



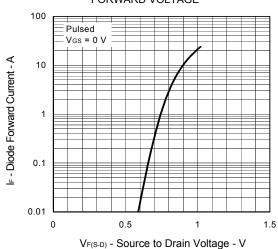
Tch - Channel Temperature - °C

SWITCHING CHARACTERISTICS

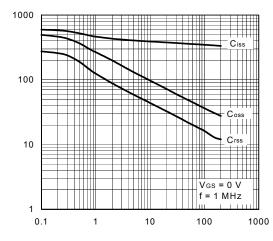


Ip - Drain Current - A

SOURCE TO DRAIN DIODE FORWARD VOLTAGE



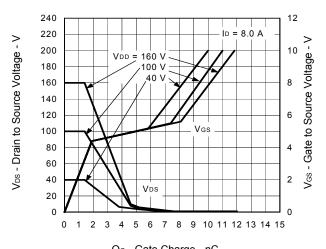
CAPACITANCE vs.
DRAIN TO SOURCE VOLTAGE



Ciss, Coss, Crss - Capacitance - pF

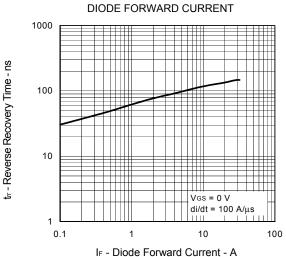
V_{DS} - Drain to Source Voltage - V

DYNAMIC INPUT/OUTPUT CHARACTERISTICS

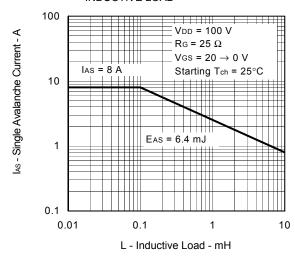


Q_G - Gate Charge - nC

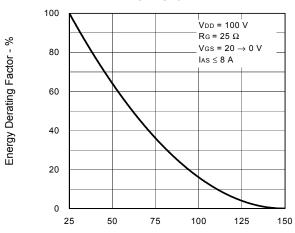
REVERSE RECOVERY TIME vs.



查询"2SK3635"快应商ALANCHE CURRENT vs. INDUCTIVE LOAD



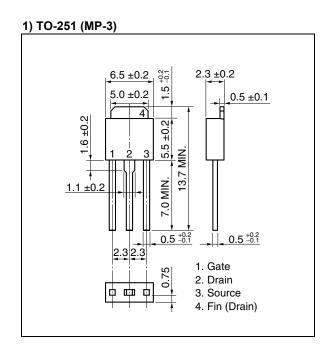
SINGLE AVALANCHE ENERGY DERATING FACTOR

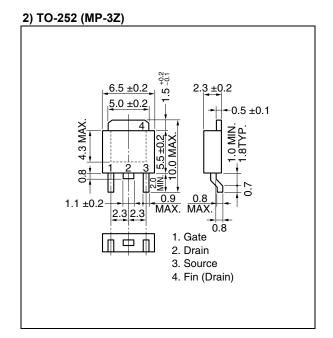


Starting T_{ch} - Starting Channel Temperature - $^{\circ}C$

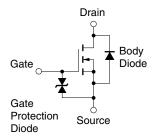


★查询"28K3625"供证的GS (Unit: mm)





EQUIVALENT CIRCUIT



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD.

When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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查询"2SK3635"供应商

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